



GP2M002A060HG Information



For Reference Only

Part Number GP2M002A060HG

Manufacturer Global Power Technologies Group

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 2A TO220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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GP2M002A060HG Specifications

Manufacturer Part Number GP2M002A060HG Manufacturer Global Power Technologies Group Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 2A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 9nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 360pF @ 25V Vgs (Max) ± 30V FET Feature - Power Dissipation (Max) 52.1W (Tc) Rds On (Max) @ Id, Vgs 4 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3		
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Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C2A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs9nC @ 10VInput Capacitance (Ciss) (Max) @ Vds360pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)52.1W (Tc)Rds On (Max) @ Id, Vgs4 Ohm @ 1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C2A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs9nC @ 10VInput Capacitance (Ciss) (Max) @ Vds360pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)52.1W (Tc)Rds On (Max) @ Id, Vgs4 Ohm @ 1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C2A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs9nC @ 10VInput Capacitance (Ciss) (Max) @ Vds360pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)52.1W (Tc)Rds On (Max) @ Id, Vgs4 Ohm @ 1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Series	-
Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C2A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs9nC @ 10VInput Capacitance (Ciss) (Max) @ Vds360pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)52.1W (Tc)Rds On (Max) @ Id, Vgs4 Ohm @ 1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) #30V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4 Ohm @ 1A, 10V Operating Temperature Supplier Device Package Package / Case 2A (Tc) 2A (Tc) 2A (Tc) 2A (Tc) 4 Ohm 10V 5V @ 250μA 5V @ 25V 4 Ohm 10V 52.1W (Tc) Through Hole TO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id St @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs A Ohm @ 1A, 10V Operating Temperature Supplier Device Package Package / Case TO-220-3	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 5V @ 250μA 50 Q 10V 360pF @ 25V ±30V 52.1W (Tc) 4 Ohm @ 1A, 10V Through Hole Through Hole TO-220 TO-220-3	Current - Continuous Drain (Id) @ 25°C	2A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ETF Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Joperating Type Through Hole Supplier Device Package Package / Case Pnoc @ 10V 360pF @ 25V ±30V £30V £30V FET Feature	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Through Hole Supplier Device Package Package / Case 360pF @ 25V 430V	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)52.1W (Tc)Rds On (Max) @ Id, Vgs4 Ohm @ 1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	9nC @ 10V
FET Feature - Power Dissipation (Max) 52.1W (Tc) Rds On (Max) @ Id, Vgs 4 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	360pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs4 Ohm @ 1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Power Dissipation (Max)	52.1W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	4 Ohm @ 1A, 10V
Supplier Device Package TO-220 Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220
Report errors?	Package / Case	TO-220-3
		Report errors?

GP2M002A060HG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

GP2M002A060HG Payment Methods



















GP2M002A060HG Shipping Methods













If you have any question about GP2M002A060HG, please do not hesitate to contact us!

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